

Abstracts

Operating Characteristics of 2-8 GHz GaAs MESFET Amplifiers at Elevated Case Temperatures to 200 Degrees Centigrade

E.J. Crescenzi, Jr., J.A. Thompson, T.R. Kritzer and M.E. Kretschmar. "Operating Characteristics of 2-8 GHz GaAs MESFET Amplifiers at Elevated Case Temperatures to 200 Degrees Centigrade." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 837-840.

RF performance of 2-8 GHz amplifiers utilizing GaAs MESFETs which incorporate TiWN diffusion barriers is reported for a case temperature range of -54 to +200°C. Preliminary results of in-process accelerated life tests are also included.

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